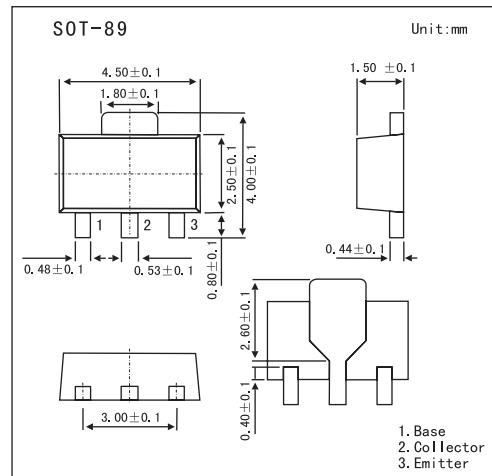


2SA1734

■ Features

- Low saturation voltage: $V_{CE(sat)} = -0.5$ V (max) ($I_C = -700$ mA).
- High speed switching time: $t_{stg} = 0.2\mu s$ (typ.).
- Small flat package.
- $PC = 1.0$ to 2.0 W (mounted on ceramic substrate).



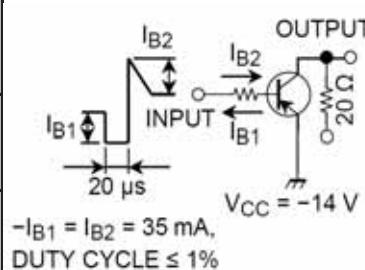
■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-40	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-2	A
Base current	I_B	-1.2	A
Collector power dissipation	P_C	500	mW
	P_C^*	1000	
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to +150	°C

* Mounted on ceramic substrate (250 mm² X 0.8 t)

2SA1734

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = -40 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -6 V, I _C = 0			-0.1	μA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10 mA, I _B = 0	-50			V
DC current gain	h_{FE}	V _{CE} = -2 V, I _C = -100 mA	120		400	
		V _{CE} = -2 V, I _C = -1.0 A	40			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = -700 mA, I _B = -35 mA			-0.5	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C = -700 mA, I _B = -35 mA			-1.2	V
Transition frequency	f _T	V _{CE} = -2 V, I _C = -100 mA	100			MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	16			pF
Turn-on time	t _{on}	 $-I_{B1} = I_{B2} = 35 \text{ mA}$, DUTY CYCLE $\leq 1\%$	0.1			μs
Storage time	t _{stg}		0.2			μs
Fall time	t _f		0.1			μs

■ Marking

Marking	LB
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